

IN THE CLAIMS:

Please cancel claims 7-13 and amend the claims as follows.

1. (Currently Amended) A cleaning method for a vapor phase deposition apparatus for forming film onto a substrate by introducing film forming gas into a chamber via a shower head, comprising:

~~a step of~~ activating a cleaning gas including a compound containing fluorine atoms by exposure to microwaves, and introducing the ~~radicals of said~~ cleaning gas into said a chamber; and

~~a step for~~ raising the a temperature of said a shower head to a temperature greater than that used when forming a film on said a substrate; and removing a deposit comprising tungsten and silicon.

2. (Currently Amended) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein raising the temperature of the shower head comprises restricting a supply of a cooling medium to said chamber for cooling said the shower head is restricted.

3. (Currently Amended) A cleaning method for a vapor phase deposition apparatus according to claim 2, wherein ~~heat is applied to said~~ raising the temperature of the shower head further comprises heating the shower head by a heater.

4. (Currently Amended) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein ~~heat is applied to said~~ raising the temperature of the shower head comprises heating the shower head by a heater.

5. (Currently Amended) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein the temperature of said the shower head is raised to about 50°C or above.

6. (Currently Amended) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein ~~said~~ the film forming gas includes gas consisting of a compound containing tungsten atoms, and the temperature of ~~said~~ the shower head is raised to about 70°C or above.

7-13. (Canceled)